Claims

[c1]   1.A method of defect review comprising following steps:

providing a wafer with a plurality of defects;

performing a defect inspection to detect the defects;

performing an automatic defect classification according

to a database to separate the defects into a plurality of

defect types; and

performing a defect review;

wherein each defect type has different sampling ratios in

the defect review according to its influence degree of

process yield.

[c2]   2.The method of claim 1 wherein the database comprises

information about the plurality of defect types and defect

information corresponding to each defect type.

[c3]   3.The method of claim 2 wherein the defect information

comprises the influence degree of the process yield of

each defect type.

[c4]   4.The method of claim 3 wherein the database separates

the defect types into killer defects and non-killer defects

according to the influence degree of the process yield.

[c5]   5.The method of claim 4 wherein the sampling ratio of the killer defects in the defect review is larger than that of the non-killer defects.

[c6]   6.The method of claim 3 wherein the database separates the defects into pre-layer defects and adding defects, and further separates the adding defects into killer defects and non-killer defects.

[c7]   7.The method of claim 6 wherein the defect review focuses on the adding defects.

[c8]   8.The method of claim 1 wherein after finishing the defect inspection, a judgment of cluster defects is performed and a defect review with a high sampling ratio is performed on the cluster defects if the cluster defects exist.

[c9]   9.The method of claim 1 wherein the database is updated according to the result of the defect review after finishing the defect review.